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Renesas Technology Corp.
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April 1, 2003

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HM62L36256 Series

9M Synchronous Fast Static RAM
(256k-word × 36-bit)

ADE-203-1318A (Z)
Rev.1.0
Dec. 14, 2001

Description

The HM62L36256 is a synchronous fast static RAM organized as 256-kword × 36-bit. It has realized high speed access time by employing the most advanced CMOS process and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. It is packaged in standard 119-bump BGA.

Note: All power supply and ground pins must be connected for proper operation of the device.

Features

- 2.5V ± 5% and 3.3V ± 3% Operation
- Synchronous register to register Operation
- Internal self-timed late write
- Byte Write Control (4 byte write selects, one for each 9-bit)
- Optional ×18 configuration
- HSTL compatible I/O
- Programmable impedance output drivers
- Differential HSTL Clock Inputs
- Asynchronous $\overline{G}$ Output Control
- Asynchronous sleep mode
- FC-BGA 119pin Package with SRAM JEDEC Standard Pinout
- Limited set of boundary scan JTAG IEEE 1149.1 compatible

Ordering Information

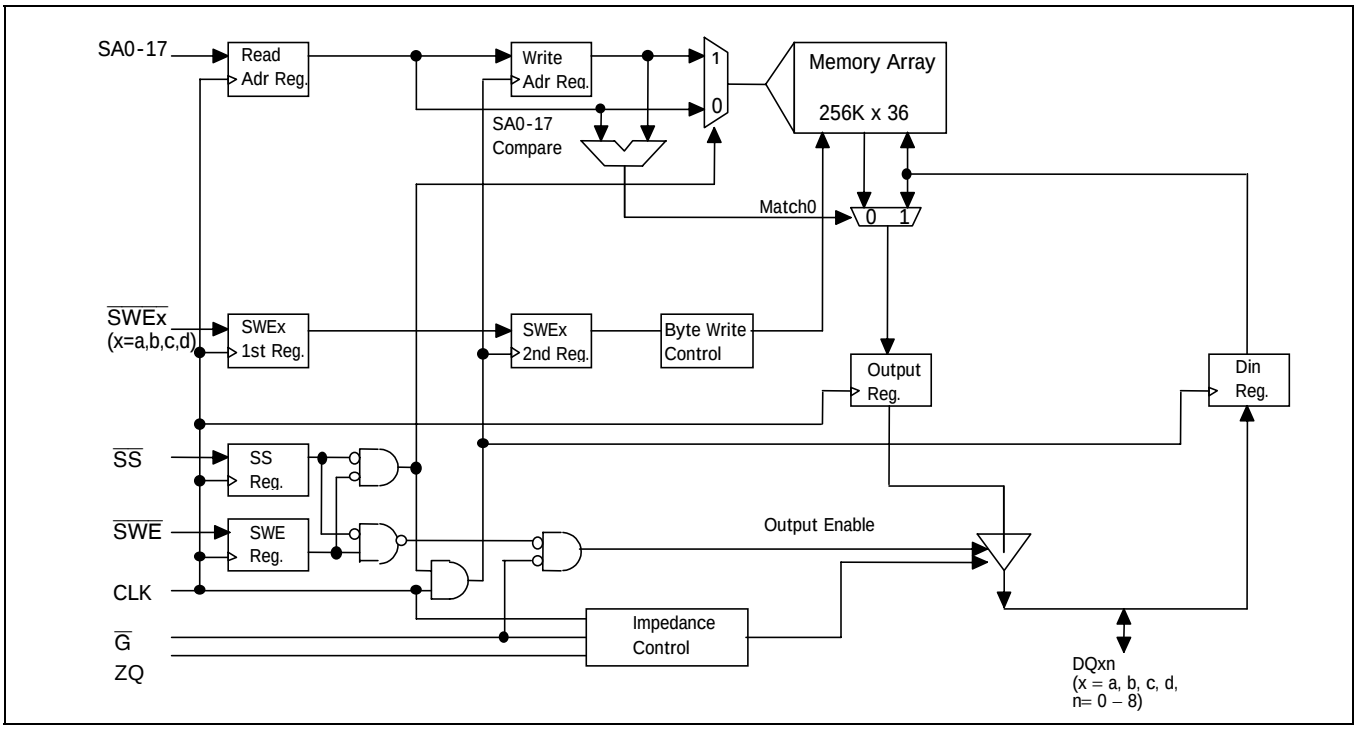
Type No.	Organization	Access time	Cycle time	Package
HM62L36256BP-28	256k × 36	1.6 ns	2.85 ns	119-bump 1.27 mm
HM62L36256BP-33	256k × 36	1.7 ns	3.3 ns	14 mm × 22 mm BGA (BP-119C)

Pin Arrangement

	1	2	3	4	5	6	7
A	V_{DDQ}	SA0	SA1	NC	SA13	SA12	V_{DDQ}
B	NC	NC	SA2	NC	SA14	SA11	NC
C	NC	SA3	SA4	V_{DD}	SA5	SA6	NC
D	DQc5	DQc0	V_{SS}	ZQ	V_{SS}	DQb0	DQb5
E	DQc4	DQc3	V_{SS}	$\overline{SS}$	V_{SS}	DQb3	DQb4
F	V_{DDQ}	DQc1	V_{SS}	$\overline{G}$	V_{SS}	DQb1	V_{DDQ}
G	DQc8	DQc6	$\overline{SWEc}$	NC	$\overline{SWEb}$	DQb6	DQb8
H	DQc7	DQc2	V_{SS}	NC	V_{SS}	DQb2	DQb7
J	V_{DDQ}	V_{DD}	V_{REF}	V_{DD}	V_{REF}	V_{DD}	V_{DDQ}
K	DQd7	DQd2	V_{SS}	K	V_{SS}	DQa2	DQa7
L	DQd8	DQd6	$\overline{SWEd}$	$\overline{K}$	$\overline{SWEa}$	DQa6	DQa8
M	V_{DDQ}	DQd1	V_{SS}	$\overline{SWE}$	V_{SS}	DQa1	V_{DDQ}
N	DQd4	DQd3	V_{SS}	SA8	V_{SS}	DQa3	DQa4
P	DQd5	DQd0	V_{SS}	SA10	V_{SS}	DQa0	DQa5
R	NC	SA7	M1	V_{DD}	M2	SA15	NC
T	NC	NC	SA9	SA16	SA17	NC	ZZ
U	V_{DDQ}	TMS	TDI	TCK	TDO	NC	V_{DDQ}

(Top view)

Block Diagram



Pin Descriptions

Name	I/O type	Descriptions	Notes
V_{DD}	Supply	Core Power Supply	
V_{SS}	Supply	Ground	
V_{DDQ}	Supply	Output Power Supply	
V_{REF}	Supply	Input Reference: provides input reference voltage	
K	Input	Clock Input. Active high.	
$\overline{K}$	Input	Clock Input. Active low.	
$\overline{SS}$	Input	Synchronous Chip Select	
$\overline{SWE}$	Input	Synchronous Write Enable	
SAn	Input	Synchronous Address Input	n = 0-17
$\overline{SWEx}$	Input	Synchronous Byte Write Enables	x = a, b, c, d
$\overline{G}$	Input	Asynchronous Output Enable	
$\overline{ZZ}$	Input	Power Down Mode Select	
ZQ	Input	Output impedance control	1
DQxn	I/O	Synchronous Data Input/Output	x = a, b, c, d n=0, 1, 2 ... 8
M1, M2	Input	Output Protocol Mode Select	
TMS	Input	Boundary Scan Test Mode Select	
TCK	Input	Boundary Scan Test Clock	
TDI	Input	Boundary Scan Test Data Input	
TDO	Output	Boundary Scan Test Data Output	
NC	—	No Connection	

M1	M2	Protocol	Notes
V_{SS}	V_{DDQ}	Synchronous register to register operation (Late Write mode)	2

Notes: 1. ZQ is to be connected to V_{SS} via a resistance RQ where $175\Omega \leq RQ \leq 300\Omega$. If $ZQ=V_{DDQ}$ or open, output buffer impedance will be maximum.

2. There is 1 protocol with mode pin. For this application, M1 and M2 need to connect to V_{SS} and V_{DD} respectively. The state of the Mode control inputs must be set before power-up and must not change during device operation. Mode control inputs are not standard inputs and may not meet V_{IH} or V_{IL} specification. This SRAM is tested only in the synchronous register to register operation.

Truth Table

ZZ	$\overline{SS}$	$\overline{G}$	$\overline{SWE}$	$\overline{SWEa}$	$\overline{SWEb}$	$\overline{SWEc}$	$\overline{SWEd}$	K	$\overline{K}$	Operation	DQ (n)	DQ (n+1)
H	X	X	X	X	X	X	X	X	X	sleep mode	High-Z	High-Z
L	H	X	X	X	X	X	X	L-H	H-L	Dead (not selected)	X	High-Z
L	X	H	H	X	X	X	X	X	X	Dead (Dummy read)	High-Z	X
L	L	L	H	X	X	X	X	L-H	H-L	Read	X	Dout (a, b, c, d) 0-8
L	L	X	L	L	L	L	L	L-H	H-L	Write a, b, c, d byte	High-Z	Din (a, b, c, d) 0-8
L	L	X	L	H	L	L	L	L-H	H-L	Write b, c, d byte	High-Z	Din (b, c, d) 0-8
L	L	X	L	L	H	L	L	L-H	H-L	Write a, c, d byte	High-Z	Din (a, c, d) 0-8
L	L	X	L	L	L	H	L	L-H	H-L	Write a, b, d byte	High-Z	Din (a, b, d) 0-8
L	L	X	L	L	L	L	H	L-H	H-L	Write a, b, c byte	High-Z	Din (a, b, c) 0-8
L	L	X	L	H	H	L	L	L-H	H-L	Write c, d byte	High-Z	Din (c, d) 0-8
L	L	X	L	L	H	H	L	L-H	H-L	Write a, d byte	High-Z	Din (a, d) 0-8
L	L	X	L	L	L	H	H	L-H	H-L	Write a, b byte	High-Z	Din (a, b) 0-8
L	L	X	L	H	L	L	H	L-H	H-L	Write b, c byte	High-Z	Din (b, c) 0-8
L	L	X	L	H	H	H	L	L-H	H-L	Write d byte	High-Z	Din (d) 0-8
L	L	X	L	H	H	L	H	L-H	H-L	Write c byte	High-Z	Din (c) 0-8
L	L	X	L	H	L	H	H	L-H	H-L	Write b byte	High-Z	Din (b) 0-8
L	L	X	L	L	H	H	H	L-H	H-L	Write a byte	High-Z	Din (a) 0-8

Notes: 1. X means don't care for synchronous inputs, and H or L for asynchronous inputs.

2. $\overline{SWE}$, $\overline{SS}$, $\overline{SWEa}$ to $\overline{SWEd}$, SA are sampled at the rising edge of K clock.

3. Although differential clock operation is implied, this SRAM will operate properly with one clock phase (either K or $\overline{K}$) tied to V_{REF}. Under such single-ended clock operation, all parameters specified within this document will be met.

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit	Notes
Input Voltage on any pin	V_{IN}	-0.5 to V_{DDQ} + 0.5	V	1, 4
Core Supply voltage	V_{DD}	-0.5 to 3.9	V	1
Output Supply Voltage	V_{DDQ}	-0.5 to 2.2	V	1, 4
Operating Temperature	T_{OPR}	0 to 70	°C	
Storage Temperature	T_{STG}	-55 to 125	°C	
Output Short-Circuit Current	I_{OUT}	25	mA	
Latch up Current	I_{LI}	200	mA	
Package junction to case thermal resistance	θJC	2	°C/W	5, 7
Package junction to ball thermal resistance	θJB	5	°C/W	6, 7

Notes: 1. All voltage is referenced to V_{SS}.

2. Permanent device damage may occur if Absolute Maximum Ratings are exceeded. Functional operation should be restricted the Operation Conditions. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.
3. These CMOS memory circuits have been designed to meet the DC and AC specifications shown in the tables after thermal equilibrium has been established.
4. The following supply voltage application sequence is recommended: V_{SS}, V_{DD}, V_{DDQ}, V_{REF} then Vin.
   Remember, according to the Absolute Maximum Ratings table, V_{DDQ} is not to exceed 2.2V, whatever the instantaneous value of V_{DDQ}.
5. θJC is measured at the center of mold surface in fluorocarbon. (See Figure 1.)
6. θJB is measured on the center ball pad after removing the ball in fluorocarbon. (See Figure 1.)
7. These thermal resistance values have error of ±5°C/W.

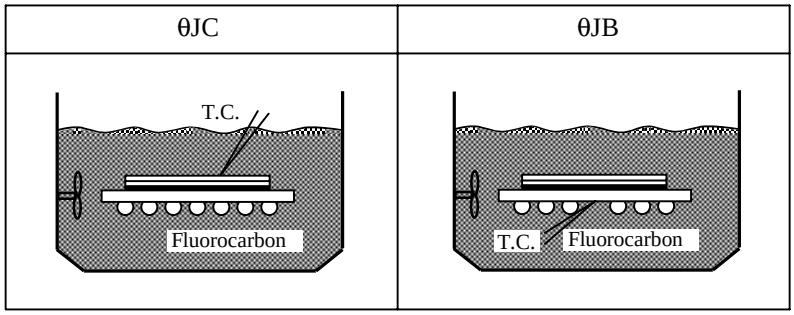


Figure 1. Definition of measurement

Note: The following the DC and AC specifications shown in the Tables, this device is tested under the minimum transverse air flow exceeding 500 linear feet per minute.

Recommended DC Operating Conditions (Ta = 0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Power Supply voltage -- Core	V_{DD}	2.38	2.5	2.63	V	2.5 V part
		3.2	3.3	3.4	V	3.3 V part
Power Supply voltage -- I/O	V_{DDQ}	1.4	1.5	1.6	V	
Input Reference Voltage -- I/O	V_{REF}	0.6	0.75	0.9	V	1
Input High Voltage	V_{IH}	V_{REF} + 0.1	—	V_{DDQ} + 0.3	V	4
Input Low Voltage	V_{IL}	–0.3	—	V_{REF} – 0.1	V	4
Clock Differential Voltage	V_{DIF}	0.1	—	V_{DDQ} + 0.3	V	2, 3
Clock Common Mode Voltage	V_{CM}	0.6	—	0.90	V	3

Notes: 1. Peak to Peak AC component superimposed on V_{REF} may not exceed 5% of V_{REF}.
2. Minimum differential input voltage required for differential input clock operation.
3. See Figure 2.
4. V_{REF} = 0.75 V (typ).

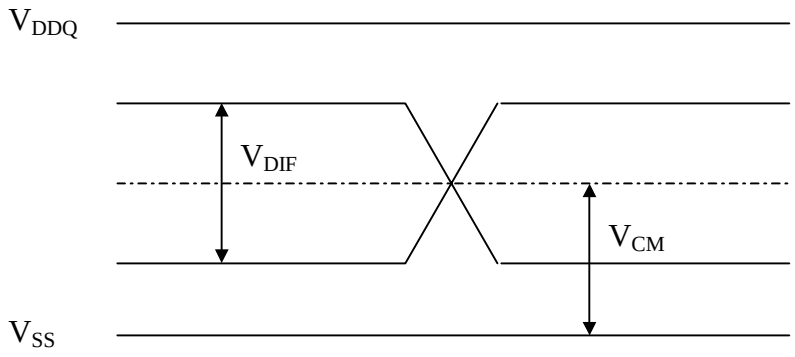


Figure 2. Differential Voltage / Common Mode Voltage

DC Characteristics (Ta = 0 to 70°C, V_{DD} = 2.5V ± 5%, 3.3V ± 3%)

Parameter	Symbol	Min	Max	Unit	Notes
Input Leakage Current	I_{LI}	—	2	µA	1
Output Leakage Current	I_{LO}	—	5	µA	2
Standby Current	I_{SBZZ}	—	128	mA	3
V_{DD} Operating Current, excluding output drivers.	I_{DD}	—	550	mA	4
Quiescent Active power supply current	I_{DD2}	—	200	mA	5
Maximum Power Dissipation, including output drivers	P	—	2.3 @ 2.5 V part	W	6
		—	2.8 @ 3.3 V part	W	6

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Output Low Voltage	V_{OL}	V_{SS}	—	V_{SS} + 0.4	V	7
Output High Voltage	V_{OH}	V_{DDQ} – 0.4	—	V_{DDQ}	V	8
ZQ pin Connect Resistance	RQ	—	250	—	Ω	
Output “Low” Current	I_{OL}	$(V_{DDQ}/2)/[\{(RQ/5 – 5\ \Omega)\}\ -15\%]$		$(V_{DDQ}/2)/[\{(RQ/5 – 5\ \Omega)\}\ +15\%]$	mA	9, 11
Output “High” Current	I_{OH}	$(V_{DDQ}/2)/[\{(RQ/5 – 5\ \Omega)\}\ +15\%]$		$(V_{DDQ}/2)/[\{(RQ/5 – 5\ \Omega)\}\ -15\%]$	mA	10, 11

Notes:
1. $0 \le Vin \le V_{DDQ}$ for all input pins (except V_{REF}, ZQ, M1, M2 pin)
2. $0 \le VOUT \le V_{DDQ}$, DQ in High–Z
3. All inputs (except clock) are held at either V_{IH} or V_{IL}, ZZ is held at V_{IH}, Iout = 0 mA. Spec is guaranteed at 75°C junction temperature.
4. Iout = 0 mA, read 75% / write 25%, $V_{DD} = V_{DD}$max, Frequency = min. cycle
5. Iout = 0 mA, read 75% / write 25%, $V_{DD} = V_{DD}$max, Frequency = 3 MHz
6. Output drives a 12pF load and switches every cycle. This parameter should be used by the SRAM designer to determine electrical and package requirements for the SRAM device
7. I_{OL} = 8 mA Minimum impedance output buffer mode
8. I_{OH} = –8 mA Minimum impedance output buffer mode
9. Measured at V_{OL}= 1/2 V_{DDQ}
10. Measured at V_{OH}= 1/2 V_{DDQ}
11. Output buffer impedance can be programmed by terminating the ZQ pin to V_{SS} through a precision resister (RQ). The value of RQ is five times the output impedance desired. The allowable range of RQ to guarantee impedance matching with a tolerance of 15% is 250 Ω typical. If the status of ZQ pin is open, output impedance is maximum. Maximum impedance occurs with ZQ connected to V_{DDQ}. The impedance update of the output driver occurs when the SRAM is in High-Z. Write and Deselect operations will synchronously switch the SRAM into and out of High-Z, therefore triggering an update. The user may choose to invoke asynchronous $\overline{G}$ updates by providing a $\overline{G}$ setup and hold about the K clock to guarantee the proper update. At power up, the output impedance defaults to minimum impedance. It will take 1024 cycles for the impedance to be completely updated if the programmed impedance is much higher than minimum impedance. The total external capacitance of ZQ pin must be less than 7.5 pF.

AC Characteristics (Ta = 0 to 70°C, V_{DD}= 2.5V ± 5%, 3.3V ± 3%)

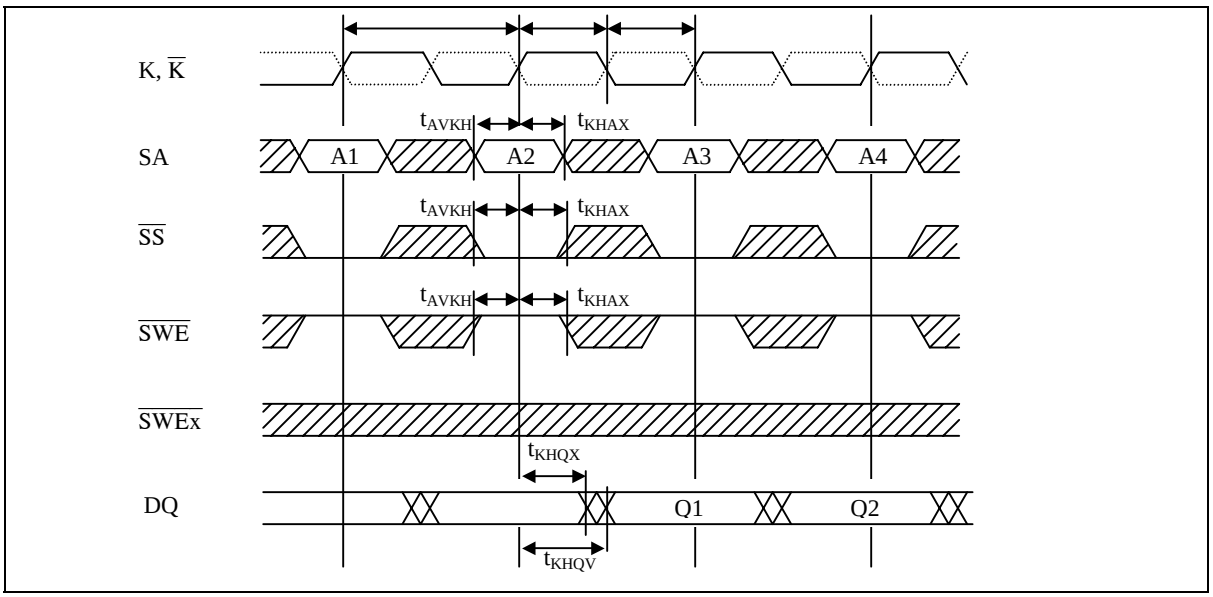
Single Differential Clock Register-Register Mode

		–28		–33			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Notes**
CK Clock Cycle time	t_{KHKH}	2.85	—	3.3	—	ns	
CK Clock High Width	t_{KHKL}	1.3	—	1.3	—	ns	
CK Clock Low Width	t_{KLKH}	1.3	—	1.3	—	ns	
Address Setup Time	t_{AVKH}	0.3	—	0.3	—	ns	2
Data Setup Time	t_{DVKH}	0.3	—	0.3	—	ns	2
Address Hold Time	t_{KHAX}	0.6	—	0.6	—	ns	
Data Hold Time	t_{KHDX}	0.6	—	0.6	—	ns	
Clock High to output valid	t_{KHQV}	—	1.6	—	1.7	ns	1
Clock High to output hold	t_{KHQX}	0.65	—	0.65	—	ns	1
Clock High to output Low-Z ($\overline{SS}$ control)	t_{KHQX2}	0.65	—	0.65	—	ns	1, 5
Clock High to output High-Z	t_{KHQZ}	0.65	2.0	0.65	2.0	ns	1, 3
Output Enable low to output Low-Z	t_{GLQX}	0.1	—	0.1	—	ns	1, 5
Output Enable low to output valid	t_{GLQV}	—	2.0	—	2.0	ns	1, 3
Output Enable high to output High-Z	t_{GHQZ}	—	2.0	—	2.0	ns	1, 3
Sleep mode recovery time	t_{ZZR}	10.0	—	10.0	—	ns	6
Sleep mode enable time	t_{ZZE}	—	9.0	—	9.0	ns	1, 3, 6

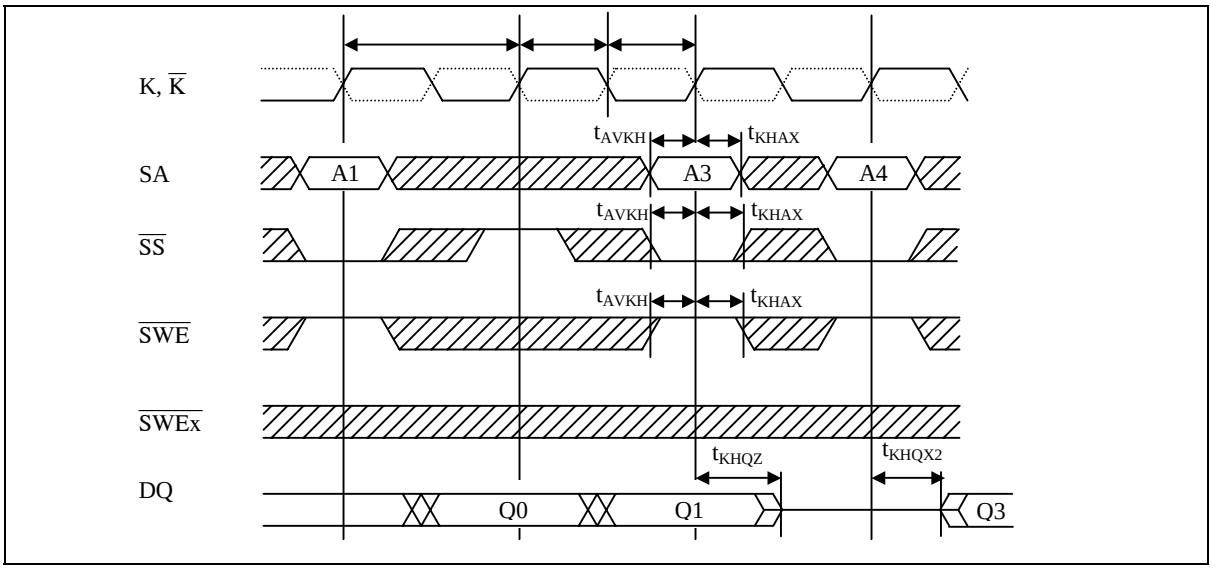
Notes: 1. See AC Test Loading figure.
2. Parameter may be guaranteed by design, i.e, without tester guardband.
3. Transitions are measured at start point of output high impedance from output low impedance.
4. Output Driver Impedance update specifications for $\overline{G}$ induced updates. Write and Deselected cycles will also induce Output Driver updates during High-Z.
5. Transitions are measured ±50 mV from steady state voltage.
6. When ZZ is switching, clock input K must be at same logic levels for reliable operation.
7. Minimum t_{KHQZ} and maximum t_{KHQV} can not occur at the same time.
8. Verified by design and tested without guardband for 3.0 ns speed sort.
9. t_{KHQX} min is verified by design and tested without guardband.

Timing Waveforms

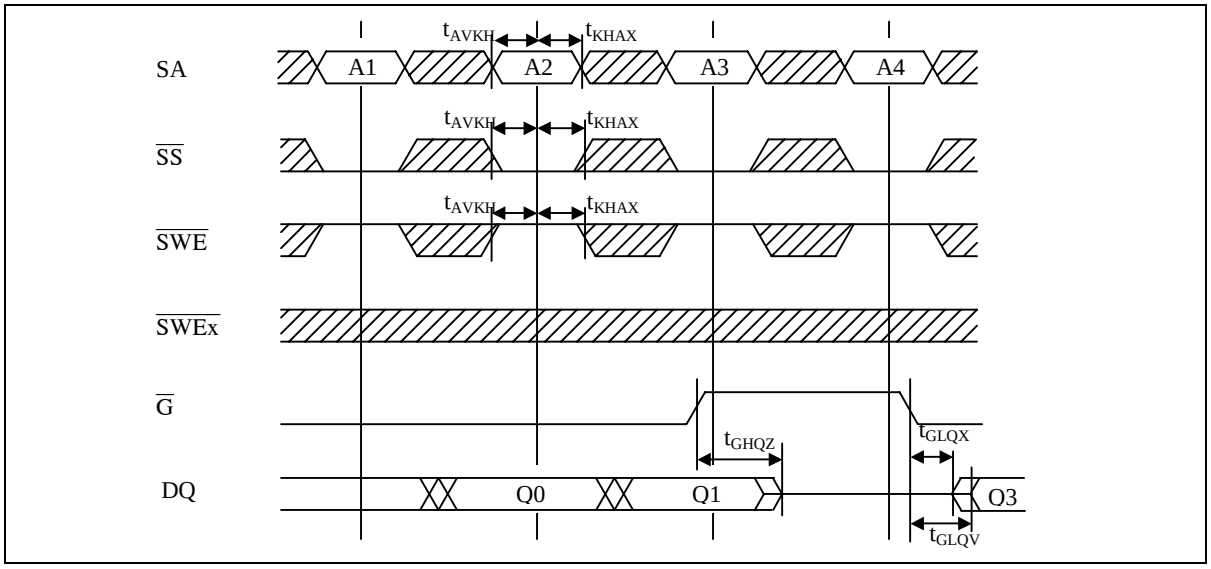
Read Cycle-1



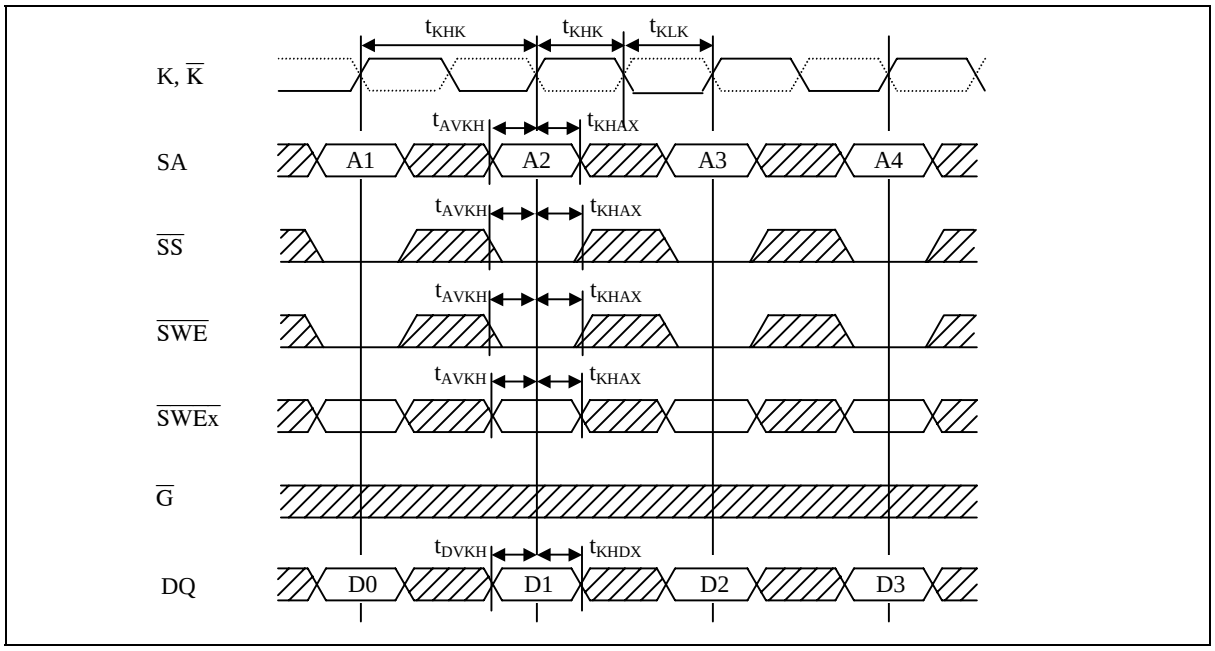
Read Cycle-2 ($\overline{SS}$ Control)



Read Cycle-3 ($\overline{G}$ Controlled)

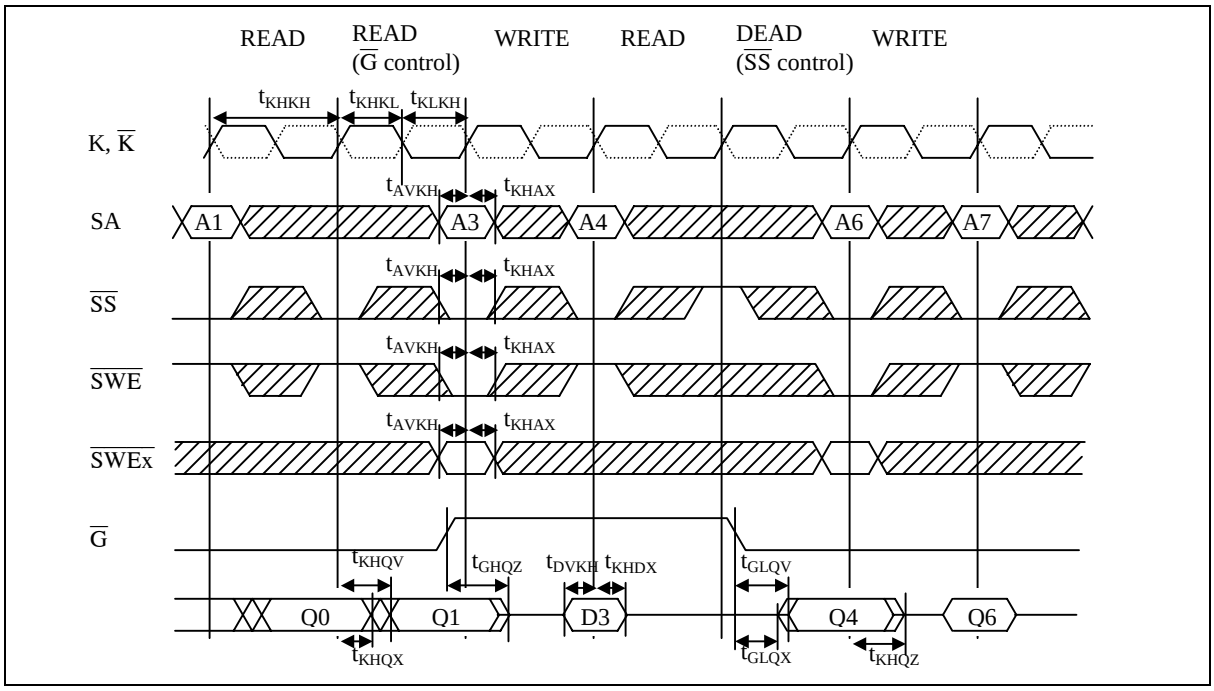


Write Cycle



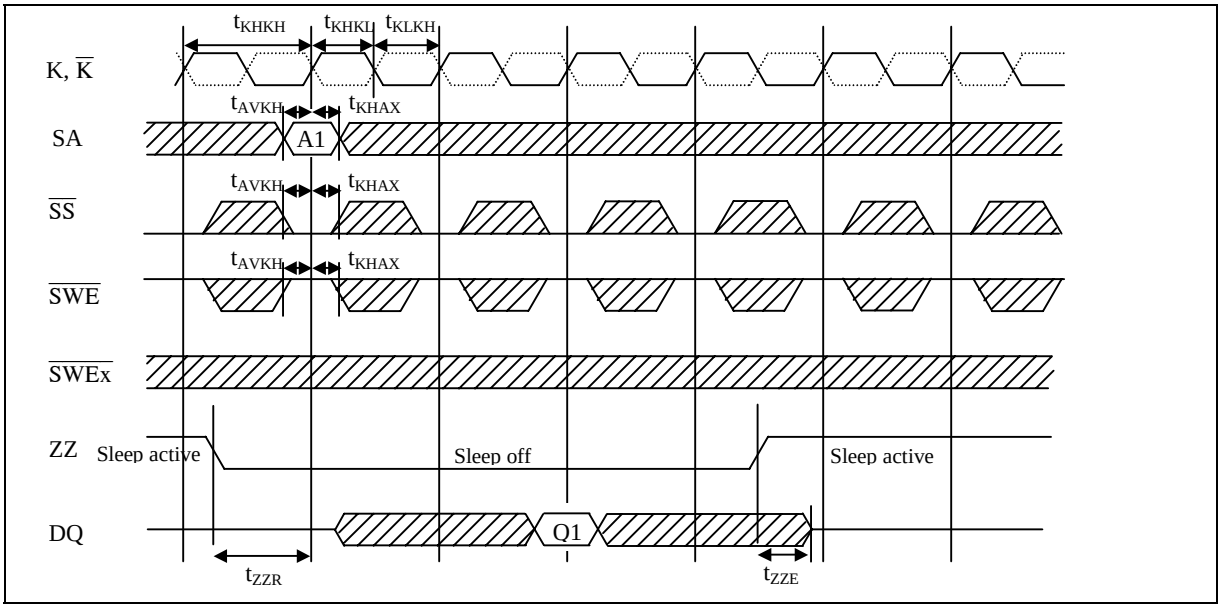
Notes: ZZ = V_{IL}, x = a, b, c, d

Read-Write Cycle



Notes: ZZ = V_{IL}, x = a, b, c, d

ZZ Control



Notes: G = V_{IL}, x = a, b, c, d

When ZZ is switching, clock input K must be at same logic levels for reliable operation.

Input Capacitance (Ta=25°C, f= 1 MHz)

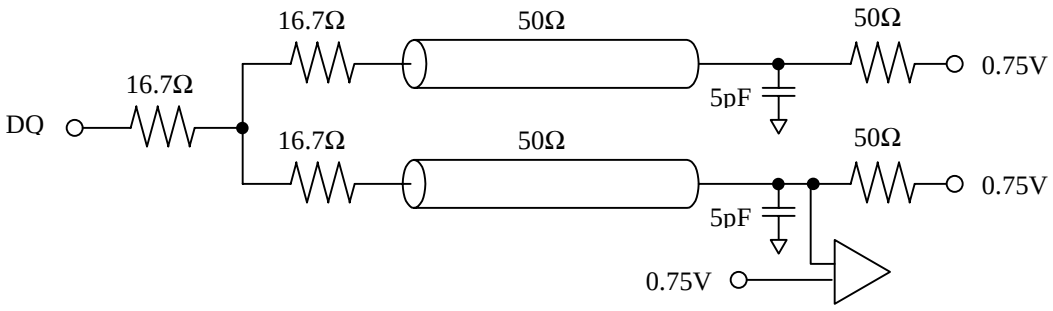
Parameter	Symbol	Min	Max	Unit	Pin name
Input Capacitance	C_{IN}	—	4	pF	SAn, $\overline{SS}$, $\overline{SWE}$, $\overline{SWEx}$
Clock Input Capacitance	C_{CLK}	—	5	pF	K, $\overline{K}$, $\overline{G}$
I/O Capacitance	C_{IO}	—	5	pF	DQxn

Note: This parameter is sampled and not 100% tested.

AC Test Conditions

Parameter	Symbol	Conditions	Unit	Note
Input and output timing reference levels	V_{REF}	0.75	V	
Input signal amplitude	V_{IL}, V_{IH}	0.25 to 1.25	V	
Input rise / fall time	tr, tf	0.5 (10% to 90%)	ns	
Clock input timing reference level		Differential Cross Point		
V_{DIF} to Clock		0.75	V	
V_{CM} to Clock		0.75	V	
Output Loading conditions		See Figures		

Note: Parameters are tested with RQ=250Ω and V_{DDQ}=1.5V.



Output Loading conditions

Boundary Scan Test Access Port Operations

Overview

In order to perform the interconnect testing of the modules that include this SRAM, the serial boundary scan test access port (TAP) is designed to operate in a manner consistent with IEEE Standard 1149.1 - 1990. But does not implement all of the functions required for 1149.1 compliance The HM62L series contains a TAP controller. Instruction register, Boundary scans register, Bypass register and ID register.

Test Access Port Pins

Symbol I/O	Name
TCK	Test Clock
TMS	Test Mode Select
TDI	Test Data In
TDO	Test Data Out

Notes: This Device does not have a TRST (TAP Reset) pin. TRST is optional in IEEE 1149.1.
To disable the TAP, TCK must be connected to Vss. TDO should be left unconnected.
To test Boundary scan, ZZ pin need to be kept below V_{REF} –0.4 V.

TAP DC Operating Characteristics (Ta = 0°C to 70°C)

Parameter	Symbol	Min	Max	Notes
Boundary scan Input High voltage	V_{IH}	2.0 V	3.6 V	
Boundary scan Input Low voltage	V_{IL}	–0.3 V	0.8 V	
Boundary scan Input Leakage Current	I_{LI}	–2 µA	+2 µA	1
Boundary scan Output Low voltage	V_{OL}	—	0.4 V	2
Boundary scan Output High voltage	V_{OH}	2.4 V	—	3

Notes: 1. $0 \le Vin \le V_{DD}$ for all logic input pin
2. I_{OL} = –8 mA at V_{DD} = 3.3 V.
3. I_{OH} = 8 mA at V_{DD} = 3.3 V.

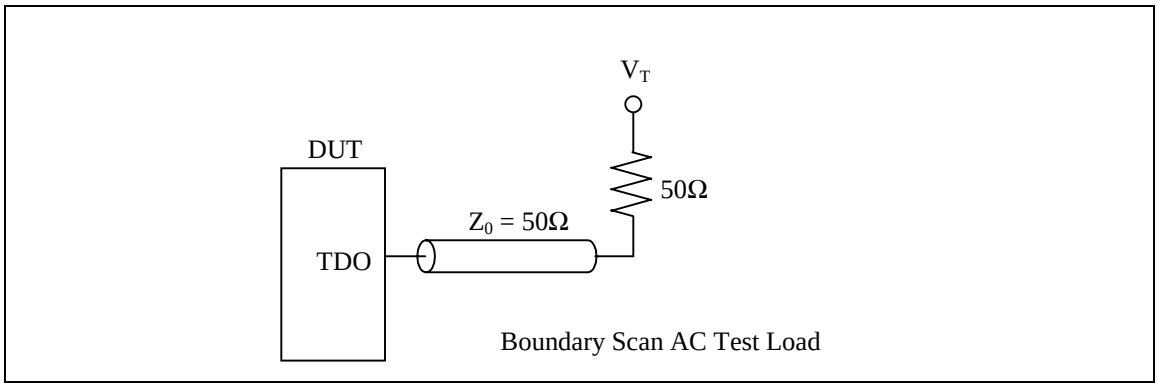
TAP AC Operating Characteristics (Ta = 0°C to 70°C)

Parameter	Symbol	Min	Max	Unit	Note
Test Clock Cycle Time	t_{THTH}	67	—	ns	
Test Clock High Pulse Width	t_{THTL}	30	—	ns	
Test Clock Low Pulse Width	t_{TLTH}	30	—	ns	
Test Mode Select Setup	t_{MVTH}	10	—	ns	
Test Mode Select Hold	t_{THMX}	10	—	ns	
Capture Setup	t_{CS}	10	—	ns	1
Capture Hold	t_{CH}	10	—	ns	1
TDI Valid to TCK High	t_{DVTH}	10	—	ns	
TCK High to TDI Don't Care	t_{THDX}	10	—	ns	
TCK Low to TDO Unknown	t_{TLQX}	0	—	ns	
TCK Low to TDO Valid	t_{TLQV}	—	20	ns	

Note: 1. t_{CS} + t_{CH} defines the minimum pause in RAM I/O pad transitions to assure pad data capture.

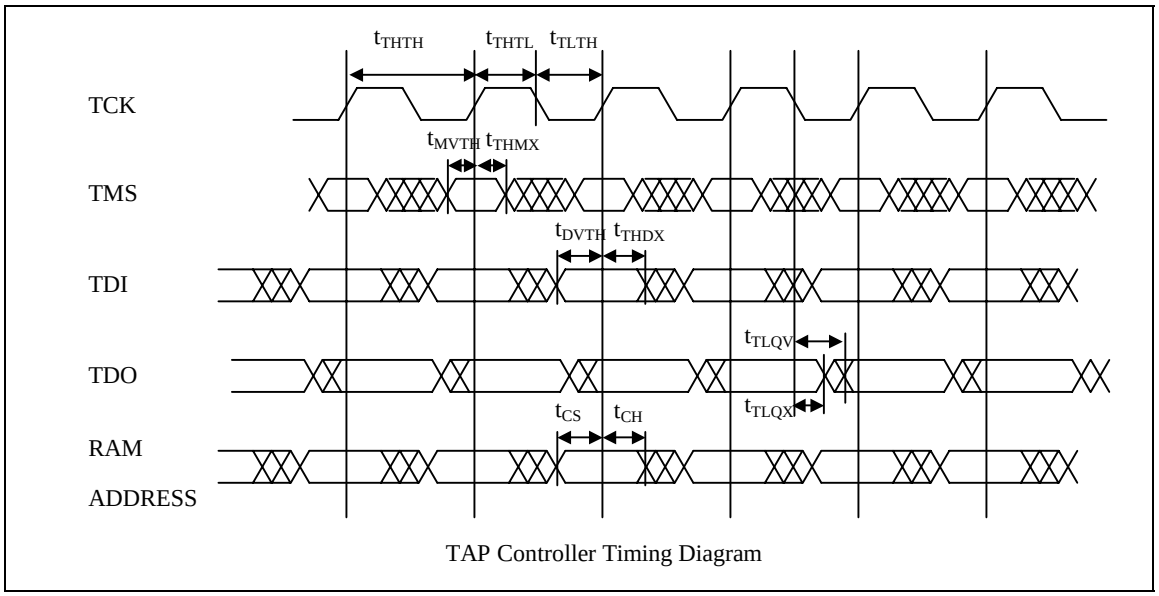
TAP AC Test Conditions (V_{DD} = 3.3 V)

- Temperature — 0°C ≤ Ta ≤ 70°C
- Input timing measurement reference Level — 1.5 V
- Input pulse levels — 0 to 3.0 V
- Input Rise/Fall Time — 2.0 ns typical (10% to 90%)
- Output timing measurement reference Level — 1.5 V
- Test load termination supply voltage (V_T) — 1.5 V
- Output Load — See figures



Boundary Scan AC Test Load

TAP Controller Timing Diagram



TAP Controller Timing Diagram

Test Access Port Registers

Register Name	Length	Symbol	Note
Instruction Register	3 bits	IR [0;2]	
Bypass Register	1 bits	BP	
ID Register	32 bits	ID [0;31]	
Boundary Scan Register	70 bits	BS [1;70]	

TAP Controller Instruction Set

IR2	IR1	IR0	Instruction	Operation
0	0	0	SAMPLE-Z	Tristate all data drivers and capture the pad value
0	0	1	IDCODE	
0	1	0	SAMPLE-Z	Tristate all data drivers and capture the pad value
0	1	1	BYPASS	
1	0	0	SAMPLE	
1	0	1	BYPASS	
1	1	0	BYPASS	
1	1	1	BYPASS	

Note: This Device does not perform EXTEST, INTEST or the preload portion of the PRELOAD command in IEEE 1149.1.

Boundary Scan Order (HM62L36256)

Bit #	Bump ID	Signal name	Bit #	Bump ID	Signal name
1	5R	M2	36	3B	SA
2	4P	SA	37	2B	NC
3	4T	SA	38	3A	SA
4	6R	SA	39	3C	SA
5	5T	SA	40	2C	SA
6	7T	ZZ	41	2A	SA
7	6P	DQa	42	2D	DQc
8	7P	DQa	43	1D	DQc
9	6N	DQa	44	2E	DQc
10	7N	DQa	45	1E	DQc
11	6M	DQa	46	2F	DQc
12	6L	DQa	47	2G	DQc
13	7L	DQa	48	1G	DQc
14	6K	DQa	49	2H	DQc
15	7K	DQa	50	1H	DQc
16	5L	$\overline{\text{SWEa}}$	51	3G	$\overline{\text{SWEc}}$
17	4L	$\overline{\text{K}}$	52	4D	ZQ
18	4K	K	53	4E	$\overline{\text{SS}}$
19	4F	$\overline{\text{G}}$	54	4G	NC
20	5G	$\overline{\text{SWEb}}$	55	4H	NC
21	7H	DQb	56	4M	$\overline{\text{SWE}}$
22	6H	DQb	57	3L	$\overline{\text{SWEd}}$
23	7G	DQb	58	1K	DQd
24	6G	DQb	59	2K	DQd
25	6F	DQb	60	1L	DQd
26	7E	DQb	61	2L	DQd
27	6E	DQb	62	2M	DQd
28	7D	DQb	63	1N	DQd
29	6D	DQb	64	2N	DQd
30	6A	SA	65	1P	DQd
31	6C	SA	66	2P	DQd
32	5C	SA	67	3T	SA
33	5A	SA	68	2R	SA
34	6B	SA	69	4N	SA
35	5B	SA	70	3R	M1

Notes: 1. Bit#1 is the first scan bit to exit the chip.

2. The NC pads listed in this table are indeed no connects, but are represented in the boundary scan register by a “Place Holder”. Place holder registers are internally connected to V_{SS}.

3. In Boundary scan mode, differential input K and $\overline{\text{K}}$ are referenced to each other and must be at opposite logic levels for reliable operation.

4. ZZ must remain at V_{IL} during boundary scan.

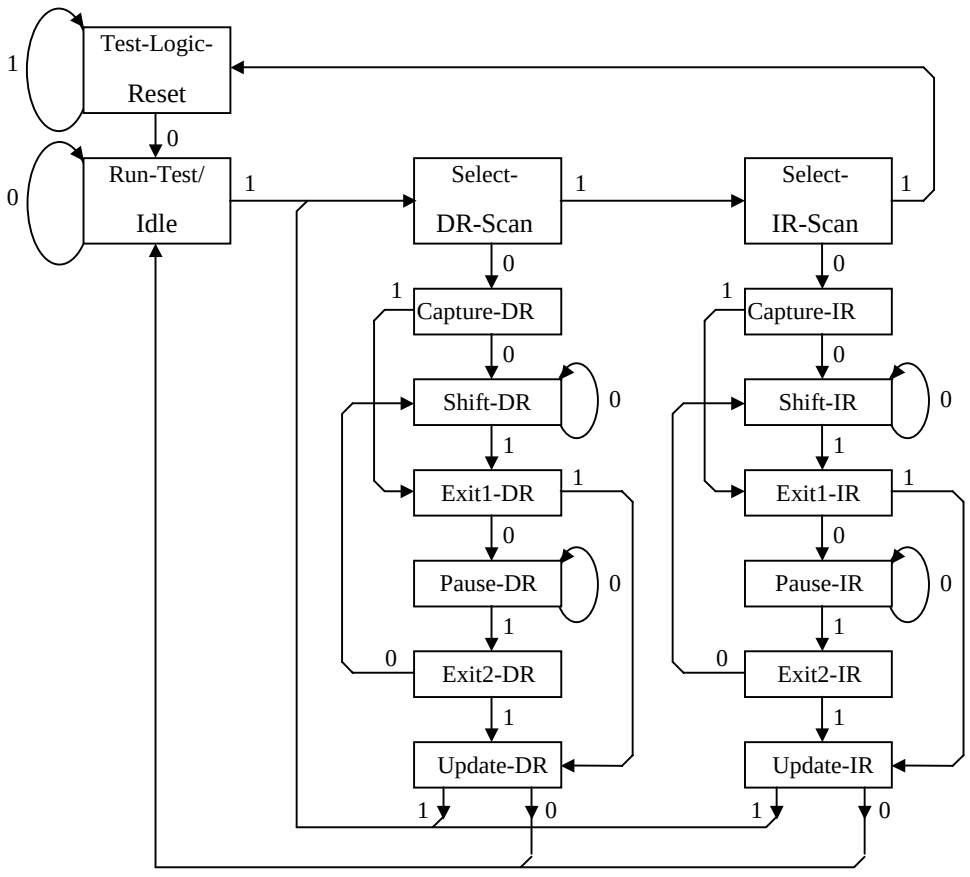
5. In boundary scan mode, ZQ must be driven to V_{DDQ} or V_{SS} supply rail to ensure consistent results.

6. M1 and M2 must be driven to V_{DD}, V_{DDQ} or V_{SS} supply rail to ensure consistent results.

ID Register

Part	Revision Number (31:28)	Device Density and Configuration (27:18)	Vendor Definition (17:12)	Vendor JEDEC Code (11:1)	Start Bit (0)
HM62L36256	0011	0011000100	xxxxxx	00000000111	1

TAP Controller State Diagram

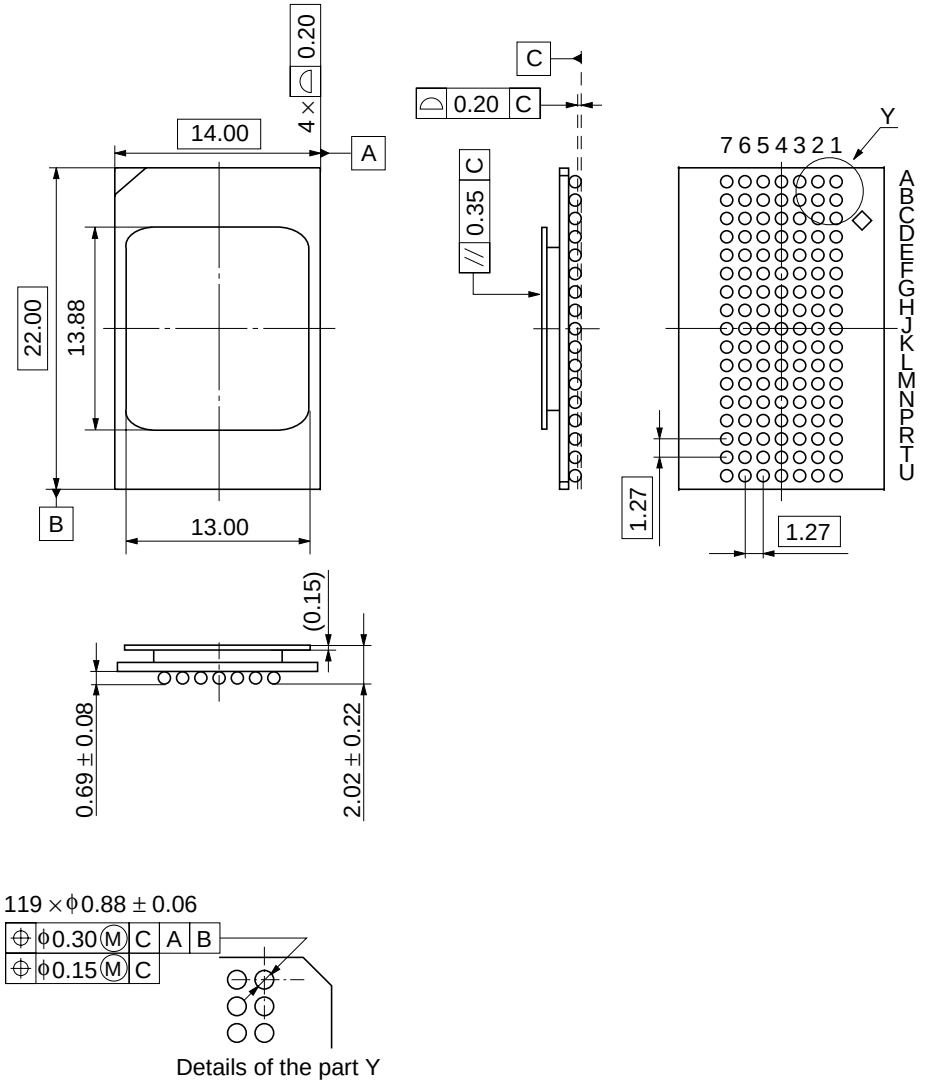


Notes: The value adjacent to each state transition in this figure represents the signal present at TMS at the time of a rising edge at TCK.
No matter what the original state of the controller, it will enter Test-Logic-Reset when TMS is held high for at least five rising edges of TCK

Package Outline

HM62L36256BP Series (BP-119C)

Unit: mm



Hitachi Code	BP-119C
JEDEC	—
EIAJ	—
Mass	1.0 g

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